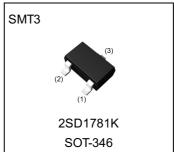


Medium Power Transistor (32V, 800mA)

Parameter	Value
V_{CEO}	32V
I _C	800mA

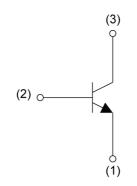
Outline



Features

- 1)Very low $V_{CE(sat)}$. $V_{CE(sat)}$ =0.1V(Typ.) (I_C/I_B =500mA/50mA)
- 2)Higt current capacity in compact package.
- 3)Complements the 2SB1197K.

•Inner circuit



- (1) Emitter
- (2) Base
- (3) Collector

Application

POWER AMPLIFIER

Packaging specifications

Part No.	Package	Package size	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit.(pcs)	Marking
2SD1781K	SMT3	2928	T146	180	8	3000	AF

● Absolute maximum ratings (T_a = 25°C)

Parameter	Symbol	Values	Unit
Collector-base voltage	V_{CBO}	40	V
Collector-emitter voltage	V_{CEO}	32	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I _C	800	mA
Collector current	I _{CP} *1	1.5	Α
Power dissipation	P _D *2	200	mW
Junction temperature	T _j	150	°C
Range of storage temperature	T _{stg}	-55 to +150	°C

● Electrical characteristics (T_a = 25°C)

Darameter	Cumbal	Conditions	Values			Lloit
Parameter	Symbol Conditions		Min.	Тур.	Max.	Unit
Collector-base breakdown voltage	BV _{CBO}	I _C = 50μA	40	-	1	V
Collector-emitter breakdown voltage	BV _{CEO}	I _C = 1mA	32	-	1	V
Emitter-base breakdown voltage	BV _{EBO}	I _E = 50μA	5	1	1	V
Collector cut-off current	I _{CBO}	V _{CB} = 20V	-	-	500	nA
Emitter cut-off current	I _{EBO}	V _{EB} = 4V	-	-	500	nA
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = 500mA, I _B = 50mA	-	100	400	mV
DC current gain	h _{FE}	V _{CE} = 3V, I _C = 100mA	120	-	390	-
Transition frequency	f _T	$V_{CE} = 5V, I_{E} = -50mA,$ f = 100MHz	-	150	-	MHz
Output capacitance	C _{ob}	V _{CB} = 10V, I _E = 0A, f = 1MHz	-	15	-	pF

hFE values are calssified as follows:

rank	Q	R	-	-	-
h _{FE}	120-270	180-390	-	-	-

^{*1} Pw=100ms Single pulse

^{*2} Each terminal mounted on a reference land.

● Electrical characteristic curves(T_a = 25°C)

Fig.1 Ground Emitter Propagation Characteristics

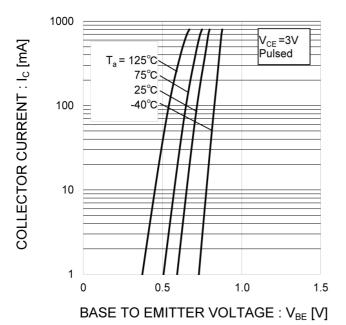
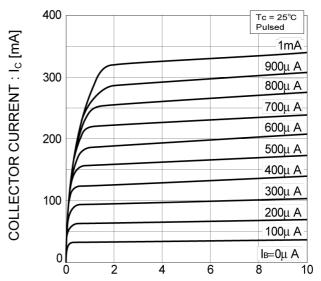


Fig.2 Typical Output Characteristics



COLLECTOR TO EMITTER VOLTAGE: V_{CE} [V]

Fig.3 DC Current Gain vs. Collector Current (I)

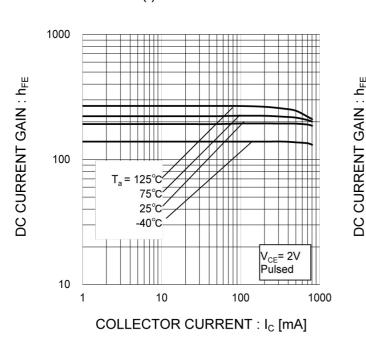
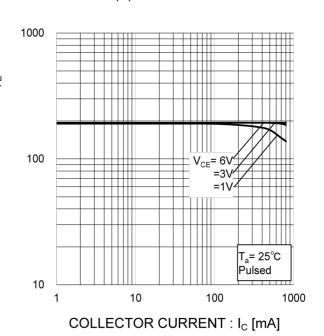


Fig.4 DC Current Gain vs. Collector Current (II)



● Electrical characteristic curves(T_a = 25°C)

Fig.5 Collector-Emitter Saturation Voltage vs. Collector Current (I)

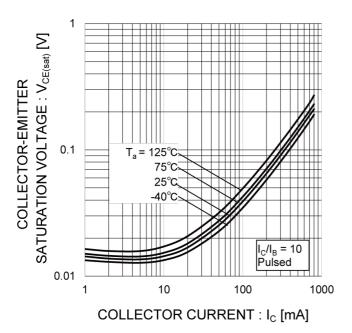


Fig.6 Collector-Emitter Saturation Voltage vs. Collector Current (II)

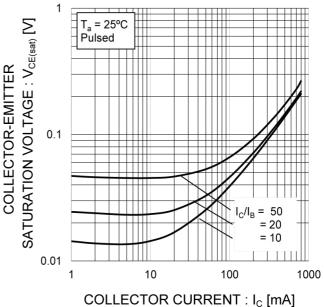


Fig.7 Base-Emitter Saturation Voltage vs. Collector Current

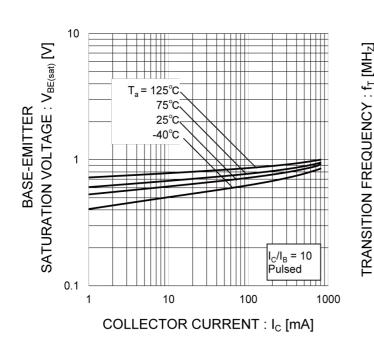
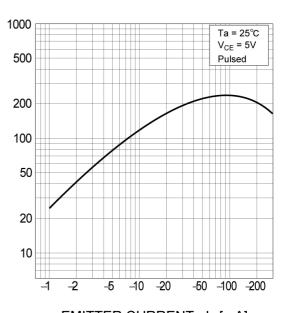


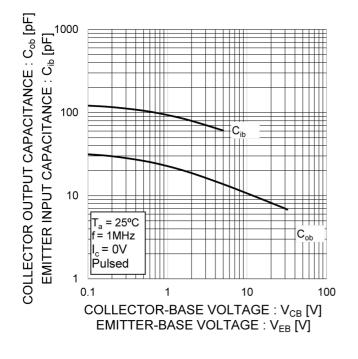
Fig.8 Gain Bandwidth Product vs. Emitter Current

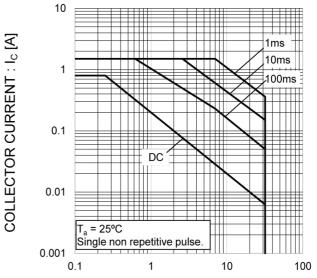


● Electrical characteristic curves(T_a = 25°C)

Fig.9 Emitter Input Capacitance vs.
Emitter-Base Voltage
Collector Output Capacitance vs.
Collector-Base Voltage

Fig.10 Safe Operating Area

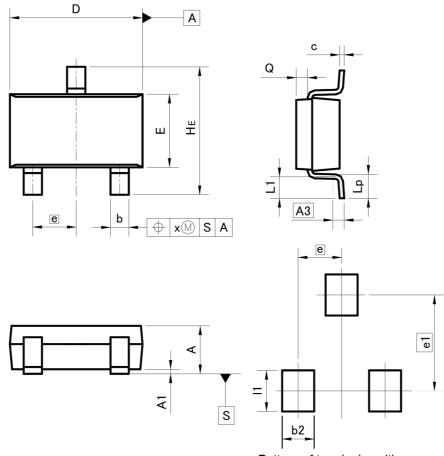




COLLECTOR TO EMITTER VOLTAGE : $V_{CE}\left[V\right]$

Dimensions

SMT3



Pattern of terminal position areas [Not a recommended pattern of soldering pads]

D.114	MILIM	ETERS	INCHES		
DIM	MIN	MAX	MIN	MAX	
Α	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0.000	0.004	
A3	0.:	25	0.0	10	
b	0.35	0.50	0.014	0.020	
С	0.09	0.25	0.004	0.010	
D	2.80	3.00	0.110	0.118	
E	1.50	1.80	0.059	0.071	
е	0.95		0.037		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.10	-	0.004	
У	_	0.10	_	0.004	

DIM	MILIM	ETERS	INCHES		
	MIN	MAX	MIN	MAX	
b2	-	0.60	-	0.024	
e1	2.	10	0.0	83	
l1	-	0.90	ı	0.035	

Dimension in mm/inches



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